

Title (en)
ACID COPPER ELECTROPLATING BATH AND METHOD FOR ELECTROPLATING LOW INTERNAL STRESS AND GOOD DUCTILITY COPPER DEPOSITS

Title (de)
SAURES KUPFERGALVANISIERUNGSBAD UND VERFAHREN ZUR GALVANISIERUNG VON KUPFERABLAGERUNGEN MIT GERINGER INNERER SPANNUNG UND GUTER DUKTILITÄT

Title (fr)
BAIN D'ÉLECTRODÉPOSITION DE CUIVRE ACIDE ET PROCÉDÉ DE GALVANISATION À FAIBLE CONTRAINTE INTERNE ET UNE BONNE DUCTILITÉ DES DÉPÔTS DE CUIVRE

Publication
EP 3141634 A1 20170315 (EN)

Application
EP 16186025 A 20160826

Priority
US 201562216054 P 20150909

Abstract (en)
Acid copper electroplating baths provide improved low internal stress copper deposits with good ductility. The acid copper electroplating baths include one or more polyallylamines and certain sulfur containing accelerators. The acid coper electroplating baths may be used to electroplate thin films on relatively thin substrates to provide thin film copper deposits having low internal stress and high ductility.

IPC 8 full level
C25D 3/38 (2006.01); **C25D 7/00** (2006.01); **C25D 7/12** (2006.01)

CPC (source: CN EP KR US)
C25D 3/38 (2013.01 - CN EP KR US); **C25D 7/00** (2013.01 - CN EP KR US); **C25D 7/12** (2013.01 - CN EP KR US); **C25D 1/04** (2013.01 - EP KR US)

Citation (applicant)

- US 6610192 B1 20030826 - STEP EUGENE N [US], et al
- US 7128822 B2 20061031 - WANG DEYAN [US], et al
- US 7374652 B2 20080520 - HAYASHI SHINJIRO [JP], et al
- US 6800188 B2 20041005 - HAGIWARA HIDEKI [JP], et al

Citation (search report)

- [XY] US 2005045486 A1 20050303 - SAHODA TSUYOSHI [JP], et al
- [XY] WO 2011151785 A1 20111208 - BASF SE [DE], et al
- [Y] SG 2012066940 A 20140428 - ROHM & HAAS ELECT MAT [US]
- [Y] US 2004104124 A1 20040603 - COBLEY ANDREW J [GB], et al

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
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DOCDB simple family (application)
EP 16186025 A 20160826; CN 201610797001 A 20160831; JP 2016174224 A 20160907; KR 20160114935 A 20160907; TW 105127930 A 20160830; US 201615238131 A 20160816